

Silicon PNP Power Transistors

2SA1887

DESCRIPTION

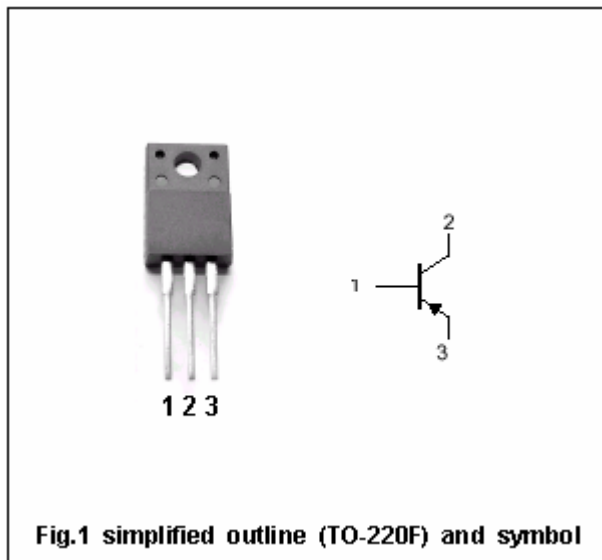
- With TO-220F package
- Low collector saturation voltage

APPLICATIONS

- High current switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-80	V
V _{CEO}	Collector-emitter voltage	Open base	-50	V
V _{EBO}	Emitter-base voltage	Open collector	-7	V
I _C	Collector current		-10	A
P _C	Collector dissipation	T _C =25°C	25	W
		T _a =25°C	2.0	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA ; I _B =0	-50			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-5A ; I _B =-0.25A		-0.2	-0.4	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-5A ; I _B =-0.25A		-0.95	-1.4	V
I _{CBO}	Collector cut-off current	V _{CB} =-70V ; I _E =0			-1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V ; I _C =0			-1.0	μA
h _{FE}	DC current gain	I _C =-1A ; V _{CE} =-1V	120		400	
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =-10V ; f=1MHz		215		pF
f _T	Transition frequency	I _C =-1A ; V _{CE} =-1V		45		MHz

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PACKAGE OUTLINE

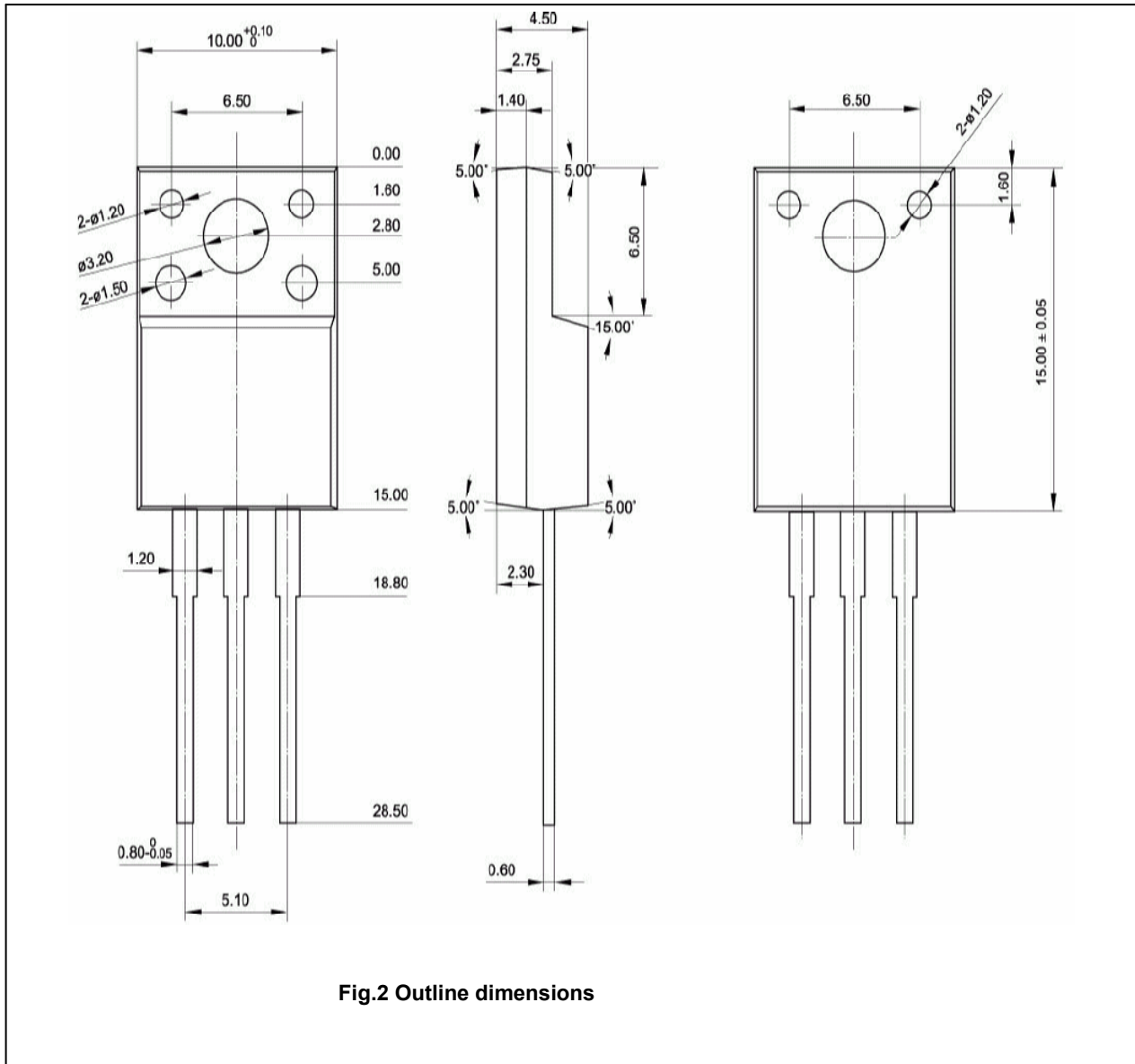


Fig.2 Outline dimensions